DYNEX SEMICONDUCTOR

TF944..H

Fast Switching Thyristor

Replaces January 2000 version, DS4281-4.0

DS4281-4.1 July 2002

APPLICATIONS

- High Power Inverters And Choppers
- UPS
- Railway Traction
- Induction Heating
- AC Motor Drives
- Cycloconverters

KEY PARAMETERS

V_{DRM}	**3500V**
$I_{T(RMS)}$	**1350A**
I_{TSM}	**13000A**
dV/dt	**500V/µs**
dI/dt	**500A/µs**
t_q	**120µs**

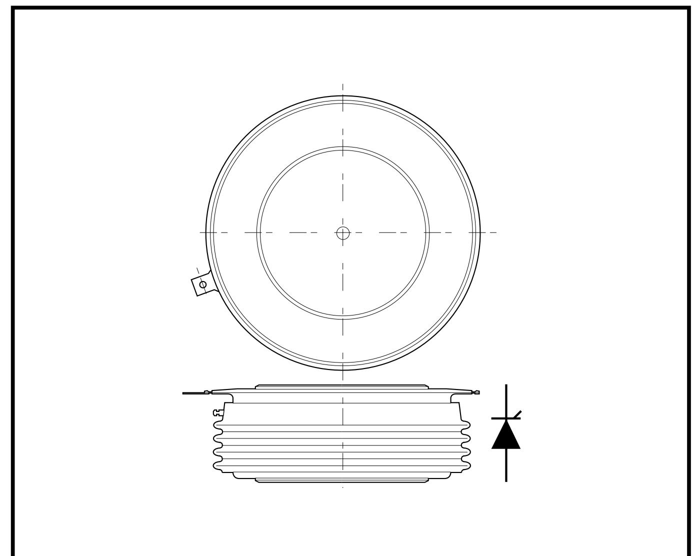
FEATURES

- Double Side Cooling
- High Surge Capability
- High Voltage

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM}	Conditions
TF944 35H TF944 34H TF944 32H TF944 30H	3500 3400 3200 3000	$V_{RSM} = V_{RRM}$ + 100V $I_{DRM} = I_{RRM}$ = 100mA at V_{RRM} or V_{DRM} & T_{vj}

Lower voaltage grades available.



Outline type code: MU169
See Package Details for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
$I_{T(AV)}$	Mean on-state current	Half sinewave, 50Hz, T_{case} = 80°C	850	A
$I_{T(RMS)}$	RMS value	Half sinewave, 50Hz, T_{case} = 80°C	1350	A

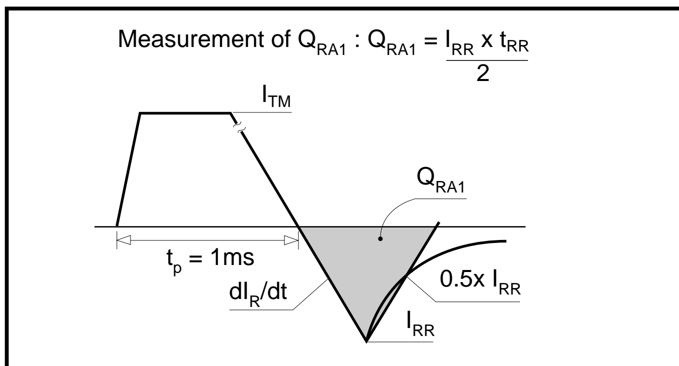
SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; V_R = 0% V_{RRM}, T_j = 125˚C	13.0	kA
I^2t	I^2t for fusing	10ms half sine; V_R = 0% V_{RRM}, T_j = 125˚C	845 x 10^3	A^2s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.02	°C/W
		Single side cooled	Anode dc	-	-	°C/W
			Cathode dc	-	-	°C/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 23.5kN with mounting compound	Double side	-	0.006	°C/W
			Single side	-	0.012	°C/W
T_{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T_{stg}	Storage temperature range			-40	150	°C
-	Clamping force			22.3	24.6	kN

MEASUREMENT OF RECOVERED CHARGE - Q_{RA1}



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Min.	Max.	Units
V_{TM}	Maximum on-state voltage	At 1500A peak, T_{case} = 25°C		-	2.4	V
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM}, T_{case} = 125°C		-	100	mA
dV/dt	Maximum linear rate of rise of off-state voltage	Linear to 60% V_{DRM} T_j = 125°C, Gate open circuit		-	500	V/µs
dI/dt	Rate of rise of on-state current	Gate source 20V, 20Ω	Repetitive 50Hz	-	500	A/µs
		t_r ≤ 0.5µs, T_j = 125˚C	Non-repetitive	-	800	A/µs
$V_{T(TO)}$	Threshold voltage	At T_{vj} = 125°C		-	1.35	V
r_T	On-state slope resistance	At T_{vj} = 125°C		-	0.5	mΩ
t_{gd}	Delay time	T_j = 25˚C, I_T = 50A, V_D = 300V, I_G = 1A, dI/dt = 50A/µs, dI_G/dt = 1A/µs		-	-*	µs
$t_{(ON)TOT}$	Total turn-on time			-	-*	µs
I_H	Holding current	T_j = 25°C, I_{TM} = 1A, V_D = 12V		100*	-	mA
I_H	Holding current	T_j = 25°C, I_G = 0.5A, V_D = 12V		300*	-	mA
t_q	Turn-off time	T_j = 125˚C, I_T = 500A, V_R = 100V, dV/dt = 20V/µs to 66% V_{DRM}, dI_R/dt = 50A/µs.	t_q code: H	-	120	µs
Q_{RR}	Reverse recovery charge			-	-	µC

Typical value.

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{GT}	Gate trigger voltage	V_{DRM} = 12V, T_{case} = 25°C, R_L = 6Ω	-	3.0	V
I_{GT}	Gate trigger current	V_{DRM} = 12V, T_{case} = 25°C, R_L = 6Ω	-	250	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} T_{case} = 125°C, R_L = 1kΩ	-	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V_{RGM}	Peak reverse gate voltage		-	5.0	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	-	10	A
P_{GM}	Peak gate power		-	50	W
$P_{G(AV)}$	Mean gate power		-	3.0	W

CURVES

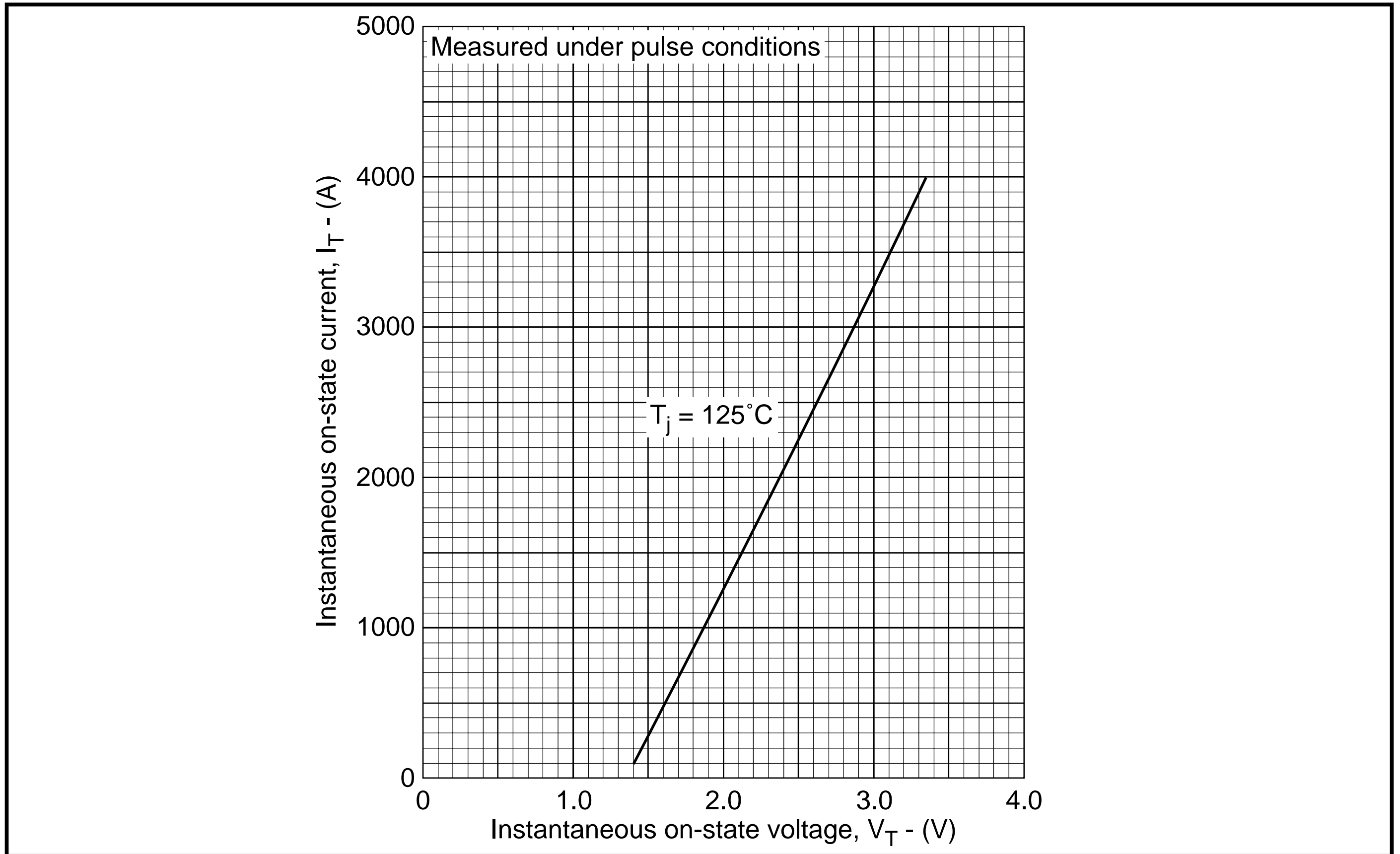


Fig.1 Maximum (limit) on-state characteristics

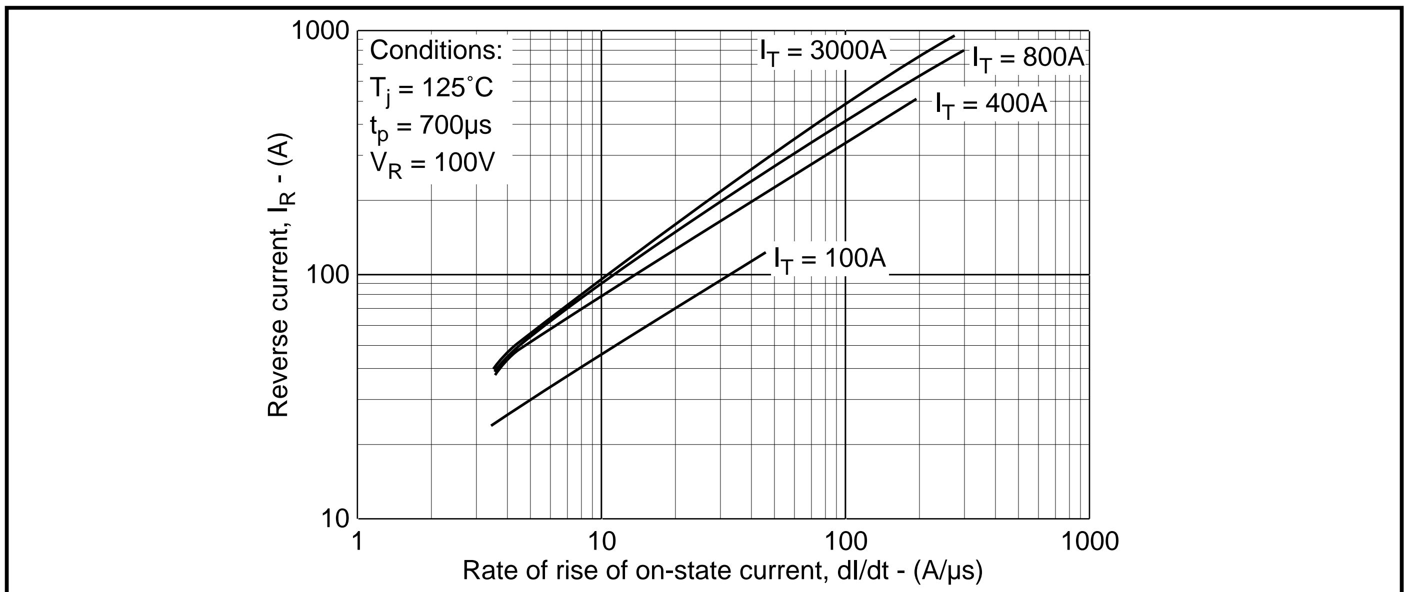


Fig.2 Reverse current vs rate of rise of on-state current

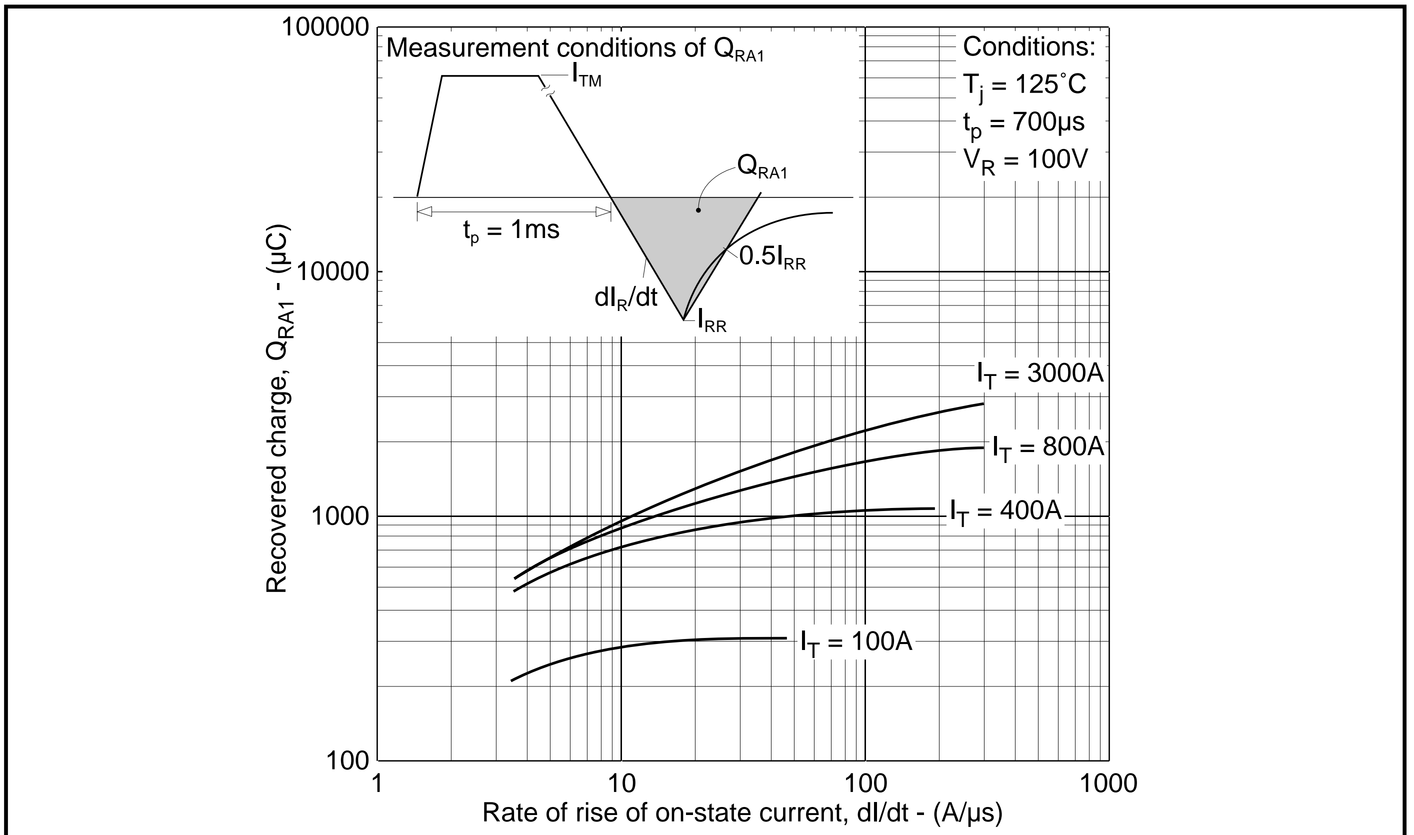
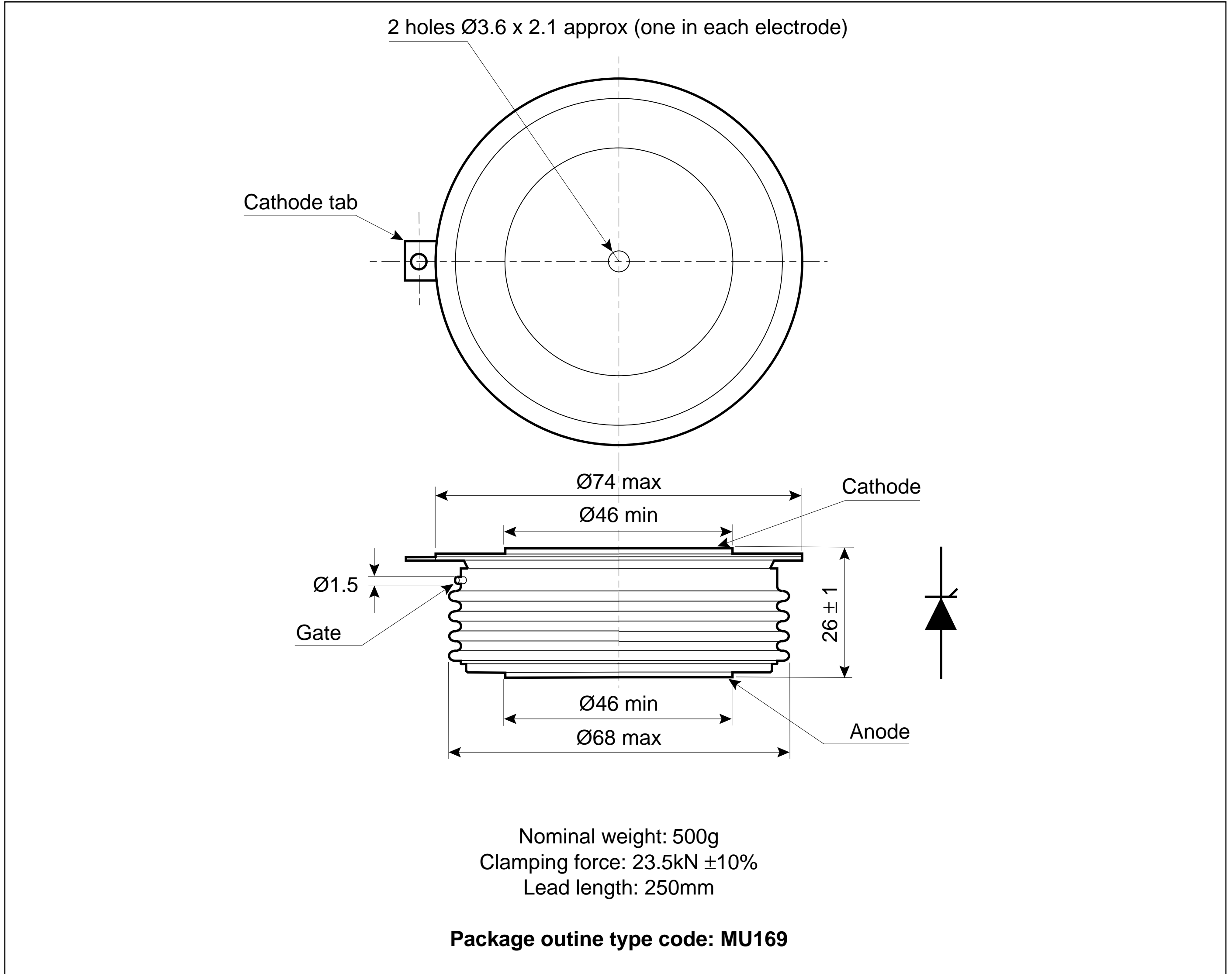


Fig.3 Recovered charge vs rate of rise of on-state current

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal weight: 500g
Clamping force: 23.5kN ±10%
Lead length: 250mm

Package outine type code: MU169

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

http://www.dynexsemi.com

e-mail: power_solutions@dynexsemi.com

HEADQUARTERS OPERATIONS
DYNEX SEMICONDUCTOR LTD
Doddington Road, Lincoln.
Lincolnshire. LN6 3LF. United Kingdom.
Tel: +44-(0)1522-500500
Fax: +44-(0)1522-500550

CUSTOMER SERVICE
Tel: +44 (0)1522 502753 / 502901. Fax: +44 (0)1522 500020

SALES OFFICES
Benelux, Italy & Switzerland: Tel: +33 (0)1 64 66 42 17. Fax: +33 (0)1 64 66 42 19.
France: Tel: +33 (0)2 47 55 75 52. Fax: +33 (0)2 47 55 75 59.
Germany, Northern Europe, Spain & Rest Of World: Tel: +44 (0)1522 502753 / 502901.
Fax: +44 (0)1522 500020
North America: Tel: (440) 259-2060. Fax: (440) 259-2059. Tel: (949) 733-3005. Fax: (949) 733-2986.

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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

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